## TOSHIBA DIODE SILICON EPITAXIAL PLANAR TYPE

# 155193

### ULTRA HIGH SPEED SWITCHING APPLICATION.

• Small Package : SC-59

• Low Forward Voltage : V<sub>F(3)</sub>=0.9V (Typ.)

• Fast Reverse Recovery Time :  $t_{rr} = 1.6ns$  (Typ.)

• Small Total Capacitance : C<sub>T</sub>=0.9pF (Typ.)

### MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	$v_{RM}$	85	V
Reverse Voltage	$V_{R}$	80	V
Maximum (Peak) Forward Current	$I_{FM}$	300	mA
Average Forward Current	IO	100	mA
Surge Current (10ms)	$I_{FSM}$	2	Α
Power Dissipation	P	150	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

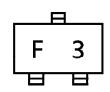
# Unit in mm | 1. ANODE | 2. N.C. | S-MINI | 3. CATHODE | JEDEC | TO-236MOD | EIAJ | SC-59 | TOSHIBA | 1-3G1B

Weight: 0.012g

# ELECTRICAL CHARACTERISTICS (Ta = 25°C)

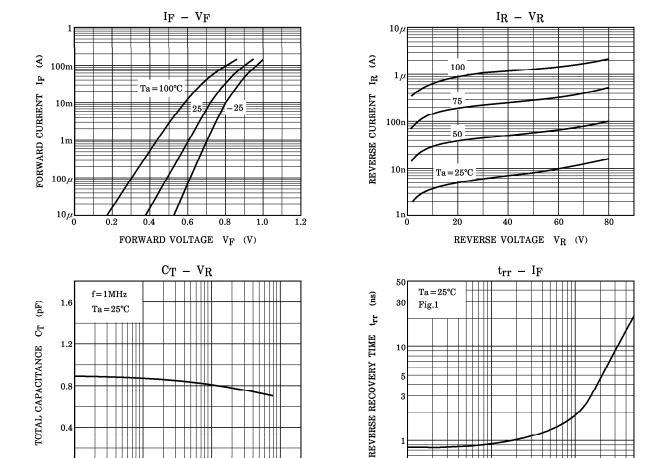
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I <sub>F</sub> =1mA	_	0.60	_	v
	$V_{F(2)}$	$I_{\mathbf{F}} = 10 \text{mA}$		0.72		
	V <sub>F (3)</sub>	$I_{\mathbf{F}} = 100 \text{mA}$	_	0.90	1.20	
Reverse Current	I <sub>R (1)</sub>	$V_R = 30V$	_	_	0.1	$\mu$ A
	I <sub>R (2)</sub>	$V_R = 80V$	_	_	0.5	
Total Capacitance	$C_{\mathbf{T}}$	$V_R=0$ , f=1MHz	_	0.9	3.0	pF
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =10mA (Fig.1)	_	1.6	4.0	ns

### **MARKING**



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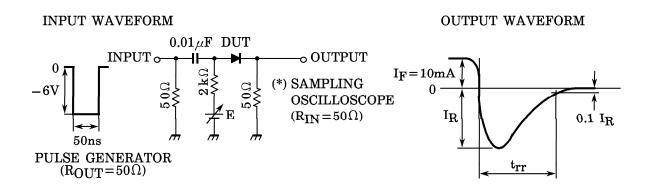


100

Fig.1 Reverse recovery time (t<sub>rr</sub>) test circuit

REVERSE VOLTAGE V<sub>R</sub> (V)

0.3



0.3

FORWARD CURRENT IF (mA)

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